

Fluctuation-Stimulated Variable-Range Hopping

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Abstract

Qualitatively new transport mechanism is suggested for hopping of carriers according to which the variable-range hopping (VRH) arises from the resonant tunneling between transport states brought into resonance by Coulomb potentials produced by surrounding sites with fluctuating occupations. A semiquantitative description of the hopping transport is given based on the assumption that fluctuations of energies of hopping sites have spectral density $1/f$.

Recently, it was suggested that fluctuations of site occupations in thermal equilibrium can cause essential energy fluctuations for sites participating in the hopping transport [1,2]. This idea was used to explain the low-frequency noise with spectral density $1/f$ reported for hopping conductivity in p-Ge(Ga) and n-Ge(As) [1]. Due to the long-range character of the Coulomb potential, fluctuations in occupation numbers of some sites lead to essential fluctuations of energies of the surrounding sites. In Refs.[1,2], an attempt has been done to distinguish between the sites participating in the hopping transport (transport sites) and fluctuators, the latter being the sites which produce energy fluctuations on the transport sites, but do not directly participate in hopping processes. Comparison of experimental data with simple theoretical estimates [2] shows that the noise level is so large that each effective resistor on the transport cluster has relative fluctuations of the

resistivity of the order unity. In the present report we study the influence of such fluctuations on the variable-range hopping.

According to the theoretical picture suggested in Refs.[1,2], the current noise is due to fluctuations of site energies affecting the hopping probabilities. The fluctuations of site energies are caused by electron transitions between sites which do not belong to the percolation cluster, but can influence the sites on the cluster by their Coulomb potentials. Thus this noise is a direct manifestation of the sequential Coulomb correlations in a hopping system suggested first by Pollak and Knotek [3,4]. The effect of these correlations on hopping transport has been discussed in numerous papers, although most studies in this field were based so far on computer simulations. Among very interesting results one can mention those of the recent study of Perez-Garrido et al. [5], who showed that the sequential correlations along with electron polarons have significant influence on the hopping conductivity in the Coulomb gap regime. Much less number of attempts have been made yet to develop analytical approaches to study the influence of sequential correlations on hopping conductivity. Ortuno and Pollak [6] were the first who considered analytically the influence of these correlations on the activation energy of hopping conductivity under the assumption of a sharp Coulomb gap. Using the mean-field theory they have shown that sequential correlations can reduce the width of the Coulomb gap Δ_C and hence diminish the activation energy of hopping conductivity.

In the present report, we study analytically the effect of sequential correlations within a somewhat different approach. Following the ideas of Refs.[1,2], we presume, that sequential correlations cause fluctuations of site energies of the effective sites on the percolation cluster with spectral density $1/f$. In general case it is difficult, if possible at all, to distinguish between transport sites and fluctuators [7] and we are not able to perform this distinguishing in the whole frequency range. However, in the limit of the high-frequency noise it is reasonable to assume [1,2] that fluctuators are represented by compact pairs of sites each pair having one electron with correspondingly high transition rate between the sites of the pair. Such pairs play the role of electronic two-level systems [2] and, as the well-known two level systems in structural glasses, lead to $1/f$ spectrum of fluctuations. Thus in this frequency region the fluctuations of energies of hopping sites are caused by hopping transitions of electrons within separated low-energy pairs surrounding the hopping sites similar to those considered by Efros et al. [8]. Below we will assume that

this $1/f$ fluctuations spectrum starting from the cut-off frequencies within the high-frequency region mentioned above is extended (with the same parameters) to much lower frequencies where the fluctuations are dominated by the aggregates of defects more complex than the isolated pairs mentioned above. Having information neither about exact picture of these aggregates nor about the character of the corresponding relaxational modes, we still believe that they support the same $1/f$ fluctuation spectrum started at high frequencies where it is supported by isolated pairs. We would like to emphasise that this assumption is decisive for the whole consideration suggested below. We cannot justify this assumption for the broad frequency range and we take it just as an ansatz. We also assume the fluctuations of site energies in the vicinity of the Fermi level to be so large that the energy positions of electrons on hopping sites within some energy strap of width $\Delta < \Delta_C$ can be arbitrary with respect to the Fermi level. In such a regime, the role of quantum mechanical resonant tunneling becomes important leading to the universal temperature-independent preexponential factor in the expression for the hopping conductivity.

An attempt to draw a picture of the phononless variable-range hopping based on the resonant tunneling has been recently made by Baranovskii and Shlimak [9]. They calculated resonant transition probabilities in the regime of strong fluctuations of site energies. They also assumed that sites with energies in the vicinity of the Fermi level have equilibrium occupations. However, the latter assumption seems not consistent with the picture of strong energy fluctuations. In the present report we try to derive the variable-range hopping transport mechanism which is not based on the equilibrium occupations.

Our main idea is the following. Due to electron transitions in the "fluctuators", the energies of sites in the vicinity of the Fermi level, i.e., of sites responsible for hopping transport at low temperatures, perform strong energy fluctuations within some effective range Δ . The energy range Δ increases with increasing fluctuation amplitudes. Sites outside this energy range possess equilibrium occupations. Transport is due to resonant transitions which occur when the fluctuating energy of a filled site within the range Δ coincides with the fluctuating energy of an empty site in this range. The critical hopping length r_c is determined by the solution of the geometrical percolation problem on random sites with concentration N_Δ , the latter being the concentration of sites in the energy strap Δ in the vicinity of the Fermi level. The amplitude of the site energy fluctuations determining Δ depends on tempera-

ture T and it is via Δ how the temperature influences the conductivity. With rising T the width Δ increases leading to the increase of the concentration N_Δ of effective sites which participate in the resonant-tunneling processes. Increasing N_Δ leads to decreasing r_c . This can be well called "the variable-range resonant tunneling" [9], because the higher is T , the shorter in space are effective hops. Below we give arguments which lead us to such picture of hopping transport.

Let us consider a pair of sites with site 1 initially occupied and site 2 initially empty. Let the activation energy for electron transition between the sites be E and the distance between the sites be R . Transition rate of an electron from site 1 to site 2 has the form

$$\nu_{1,2} = \nu_0 \exp(-2R/a - E/T) \quad (1)$$

where ν_0 is the attempt to escape frequency, a is the localisation length and temperature is measured in the units of energy. In the absence of fluctuations of site energies the typical transition time $t_{1,2}$ is determined by the condition $t_{1,2} \simeq \nu_{1,2}^{-1} \equiv t_c$. The fluctuations of the site energies can diminish the activation energy of such a pair by some amount δE . Given some spectral density of fluctuations, the quantity δE is time dependent. We assume here the spectral density of fluctuations in the form $\langle (\delta E)^2 \rangle = \alpha^2 (f_0/f)$; $f < f_0$ where f is the frequency and α, f_0 are some parameters.

We assume that fluctuations originate mainly due to pair excitations with nearly constant density of states [8]. The strongly interacting pairs form a sort of "dipolar Coulomb glass". Thus one expects that the $1/f$ spectrum extends up to very low frequencies, particularly due to the nearly-degenerate character of the ground state of the Coulomb glass [10]. The high-frequency cut-off f_0 should be related to the fastest possible modes of the dipolar glass related to hops within single pairs independent from the rest of the glass. Correspondingly, the value of α can be related to the magnitude of fluctuations originated due to these single-pair hops. We start from a phenomenological picture not specifying the values of α and f_0 and having in mind to return to this problem later.

With an account of such fluctuations the rate equation for electron transition within the chosen pair has the form

$$dn_2/dt = \nu_0 \exp(-2R/a - (E + \delta E(t))/T) n_1, \quad (2)$$

where occupation numbers n_2 and n_1 have initial values $n_1(0) = 1$; $n_2(0) = 0$. This equation has solution

$$n_2(t) = \int_0^t dt' \nu_0 \exp(-2R/a - (E + \delta E(t'))/T) n_1(t'). \quad (3)$$

Transition time t is approximately determined by the condition

$$\int_0^t dt' \nu_0 \exp(-2R/a - (E + \delta E(t'))/T) \sim 1. \quad (4)$$

The integral is obviously dominated by the smallest possible value of $\delta E(t)$. We replace the term $\delta E(t)$ in the integrand by the mean quadratic fluctuation of the activation energy $-|<\delta E(t)>|$. Using Eqs.(2), (5), one obtains for the typical transition time t

$$\alpha (\ln(tf_0))^{1/2} \sim T \ln(t_c/t). \quad (5)$$

Of course, the solution of this equation is related to the typical transition time only in the case that the latter is much longer than the time of the pure tunnelling without activation $t_h = \nu_0^{-1} \exp(2R/a)$. Combining this restriction with the formal solution of Eq.(6) one obtains

$$\ln(tf_0) = \max \left(\ln(t_h f_0); \ln(t_c f_0) - [(\alpha^2/2T^2)^2 + (\alpha/T)^2 \ln(t_c f_0)]^{1/2} + (\alpha^2/2T^2)^2 \right). \quad (6)$$

In the case $(\alpha^2/2T^2)^2 < (\alpha/T)^2 (\ln(t_c f_0))^{1/2}$ this result reflects a decrease of the effective transition time t with respect to its value t_c in the absence of fluctuations caused by the reduction of the activation energy. In that sense our result is similar to that obtained by Ortuno and Pollak [6]. If the parameters of a system under study correspond to the opposite case $\alpha^2/4T^2 > \ln(t_c f_0)$ one can use a series expansion in Eq.(6) which leads to the expression

$$\ln(tf_0) = \max \left(\ln(t_h f_0); (\ln(t_c f_0))^2 T^2 / \alpha^2 \right). \quad (7)$$

Eq.(7) shows that the transition time in the considered pair corresponds to the maximal of the two times: the time of pure tunnelling and the time necessary to nullify the activation energy for the transition. This scenario is different from the standard VRH where the logarithms of the tunneling term

and the activation terms should be compared rather than the corresponding times. We assume below that it is condition (7) that governs transition times in the pairs essential for hopping transport in the fluctuation regime.

In order to evaluate the hopping conductivity using given transition rates, one has to formulate the binding criterion for construction of the percolation cluster. Let us define the binding criterion by the condition that the time of the pure tunneling t_h in a pair is of the order of the time necessary to eliminate the activation energy E of the pair. Herewith we refuse to estimate numerical constants in the exponential terms for the hopping conductivity, though we believe that our criterion gives a correct set of parameters in the exponents in analogy to the standard variable-range hopping approach. Our criterion corresponds to the optimization procedure that leads to approximate equality of two terms in the right-hand side of Eq.(7).

In order to determine the width Δ of the energy strip in which electron transitions are responsible for transport, let us consider the density of states (DOS) function. We assume that DOS at $T = 0$ is determined by the soft Coulomb gap with quadratic energy dependence [11]:

$$g(\varepsilon) = g_0 \varepsilon^2, \quad (8)$$

where ε is the site energy measured with respect to the Fermi level. Its integral up to some energy ε determines the concentration of sites $N_\varepsilon = (2/3)g_0 \varepsilon^3$ with energies less than ε . Thus one estimates as $R_\varepsilon = cN_\varepsilon^{-1/3}$ the critical distance between the sites within the percolation cluster involving the sites from this region of energies ($c \simeq 0.87$, [11]).

Using this estimate for the first term in the right-hand side of Eq.(7) and neglecting logarithmic terms, one obtains that energy (that provides equality between two term in the r.h.s. of Eq.(7) is determined by the relation $\ln(t_h f_0) \sim (4/3)cg_0^{-1/3}\Delta^{-1}/a$. In the same way one estimates for the second term in the right-hand side of Eq.(7) $\ln(t_c f_0) \sim \Delta/T$. Thus from the binding criterion one has

$$\Delta \simeq (4cg_0^{-1/3}a^2/3a)^{1/3}. \quad (9)$$

It is worth noting that except of a numerical factor the same estimate is valid for 2D case.

According to the transport picture formulated above, the hopping conductivity is determined by the solution of the geometrical percolation problem on randomly distributed sites with concentration N_Δ . The width of the energy

strip Δ depends on temperature via the temperature dependence of parameter α . We will discuss this dependence later. Before doing so we would like to justify our transport picture by showing that in contrary to standard VRH approaches, in the suggested transport mechanism the occupation numbers of sites which form the transport path are independent on temperature and hence these occupation numbers are not essential for the calculation of the temperature dependence of the hopping conductivity.

Taking into account the explicit time dependence of the site energies one can write the rate equation for the occupation number of a site i in the form

$$\frac{dn_i}{dt} = \sum_j (W_{j,i}(\varepsilon_i(t), \varepsilon_j(t))n_j(1 - n_i) - W_{i,j}(\varepsilon_i(t), \varepsilon_j(t))n_i(1 - n_j)) \quad (10)$$

where for hopping probabilities one has $\max W_{i,j} = \max W_{j,i} = \nu_0 \exp(-2R_{i,j}/a)$. The time dependence of the probabilities does not allow to apply a simple detailed balance considerations. Moreover, the $1/f$ spectrum of the fluctuations leads to the dependence $|\delta\varepsilon| \propto \ln^{1/2}(tf_0)$ which does not allow any time averaging between the hopping events. This is a clear manifestation of non-ergodic behavior. The electron hop is prepared by the surrounding which implies memory effects instead of ergodicity.

Energy fluctuations during the typical hopping time do not allow to specify any ordering of states with respect to their energies within the energy strip Δ in the vicinity of the Fermi level. As a result, occupation numbers of those states do not correspond to the Fermi distribution being rather arbitrary. For energies outside the range Δ , fluctuations cannot suppress the energy ordering of the sites. According to the very idea of the above estimation of the hopping time t_Δ , the latter corresponds to the relaxation time of a charge in the energy strip of the width Δ (determined by Eq.(10)) and thus it characterizes the largest possible time for the charge transfer within the system. Having this in mind, one expects that the ergodicity and detailed balance considerations are restored at time scales larger than t_Δ and correspondingly for energy scales larger than Δ . Thus one obtains for the time-averaged occupation number of a state i

$$\sum_j (\langle W(\varepsilon_j, \varepsilon_i) \rangle \langle n(\varepsilon_j) \rangle (1 - \langle n(\varepsilon_i) \rangle) - \langle W(\varepsilon_i, \varepsilon_j) \rangle \cdot \langle n(\varepsilon_i) \rangle (1 - \langle n(\varepsilon_j) \rangle)) = 0 \quad (11)$$

where $\langle \rangle$ denotes the time average. For the probabilities $\langle W(\varepsilon_i, \varepsilon_j) \rangle$ one obviously has $d \langle W \rangle / d \langle \varepsilon_{i,j} \rangle|_{\varepsilon_{i,j} \rightarrow 0} \leq \langle W \rangle / \Delta$ due to averaging over instantaneous values of the energies within the relevant interval $\sim \Delta$. Thus the averaged occupation numbers $\langle n_i \rangle$ near the Fermi level correspond to a smeared Fermi distribution with effective temperature of the order of Δ . For energies $|\varepsilon| \gg \Delta$ the density of states is larger, the tunneling time is smaller and the distribution tends to the thermal one.

The fact that site occupation numbers near the Fermi level are arbitrary justifies the procedure applied above where we neglected the occupation number factors restricting ourselves to the diffusion consideration. It is also worth noting that according to the above picture, the arguments leading to the Coulomb gap [8] do not hold anymore implying that the Coulomb gap is suppressed in the energy region of the width Δ in the vicinity of the Fermi level.

In our model, hopping transitions correspond to processes in which activation energy is eliminated by fluctuations of the site energies due to correlated electron transitions in the surrounding pairs. In such a case, special attention should be devoted to resonant phononless electron transitions. Until now, we mainly discussed a preparation of the system of two sites to the electron hop rather than the hop itself. One should realize that fluctuations with spectral density $1/f$ contain contributions of all possible modes with frequencies in the range between f_0 and $1/t$, where t is the hopping time. Function $\ln^{1/2}(tf_0)$ represents a sort of "envelope function" for the fluctuation amplitudes and activation energy for a hop can vanish many times before the hop really occurs. For a pair of hopping sites 1 and 2 with energies ε_1 and ε_2 , the routine perturbation theory [13] under adiabatic conditions gives the probability p of the resonant transition during a "fluctuation period" $p \sim I^2/\hbar |(dE/dt)|^{-1}$, where I is the overlap integral $I = I_0 \exp(-2R/a)$ and $E = \varepsilon_1 - \varepsilon_2$. Making use of the random character of fluctuations and hence summing the probabilities for different "periods", one obtains for transition rate between sites 1 and 2

$$W \sim I^2/E\hbar. \quad (12)$$

Assume that our sites 1 and 2 form the effective resistor on the percolation cluster. Under applied external voltage V , dc current through the chosen resistor is equal to

$$j = eW \langle n_1(\varepsilon_1(t) + eV, t) - n_2(\varepsilon_2(t), t) \rangle \sim e^2 W V d \langle n(\varepsilon) \rangle / d\varepsilon, \quad (13)$$

where W is determined by Eq.(13). Taking into account the estimate $d < n > /d\varepsilon \sim 1/\Delta$ we come to the following expression for the hopping current

$$j \simeq (e^2/h)VI^2/\Delta^2. \quad (14)$$

The distance R in the exponent of the overlap integral I is controlled by the geometrical binding criterion discussed above.

Preexponential term I_0 of the overlap integral depends on the character of the hopping sites. For sites with the hydrogen-like Coulomb potentials $I_0 = (2e^2/3\kappa a)(r/a)$, r being characteristic hopping length, κ being the dielectric constant. In this case $I_0/\Delta \sim (r/a)^2 \gg 1$. Different situation can appear for sites with screened Coulomb potential. In the case of impurity screening $I_0 \sim e^2/\kappa r \sim \Delta$. Using this estimate for I_0 and the estimate for the exponential term in the overlap integral from Eqs.(7),(9) one obtains for the hopping conductance

$$G \simeq (e^2/h) \exp(-(T'/T)^\beta); \quad (T'/T)^\beta = (4c/3g_0^{1/3}a\alpha)^{2/3} \quad (15)$$

It can look really curious that we pretend to determine preexponential factor in the expression for hoping conductivity, while the very derivation of the exponent based on the order-of-magnitude binding criterion cannot provide us with a correct numerical factor in the exponent. However, our derivation of the preexponential factor in Eq.(15) seems to represent just a revision of the relation between diffusivity and mobility (Einstein relation) in the non-ergodic situation caused by correlated hops with $1/f$ spectrum. The crucial estimate for the above derivation is the approximate equality between I_0 and Δ , both being controlled by the Coulomb energy. The situation is to some extent similar to the standard band conduction via extended states in a Fermi system with a single characteristic energy equal to the Fermi energy.

In order to derive the values of T' and β it is necessary to specify the microscopic picture of the fluctuations which lead to the resonant transitions. Following ideas of Ref.2, we assume that the crucial parameter of the fluctuation spectrum α can be related to the fluctuation potential caused on a hopping site by the nearest soft pair with the activation energy $\sim T$. This gives the estimate $\alpha = A(\Delta_C T^2)^{1/3}$, where A is a numerical coefficient [2, 12]. Substituting this expression for α into Eq.(15), one obtains

$$\beta = 4/9, \quad T' = (4c/3Aag_0^{1/3}\Delta_C^{1/3})^{3/2}. \quad (16)$$

Note that the value $\beta = 4/9$ can hardly be distinguished experimentally from the "standard" value $\beta = 1/2$ for Efros-Shklovskii law. It can be also mentioned that for $A > 1$ the temperature T' appears to be smaller than the characteristic temperature T_1 for Efros-Shklovskii law; this fact corresponds to stimulation of the hopping by fluctuations (additional effect is related to an increase of the pre-exponential mentioned above).

The above estimate of α was based on the parabolic Coulomb gap (Eq.(8)) which is believed to exist in 3D systems. For 2D systems, pair excitations are known to be less important [11]. Nevertheless, we believe that our results can be also applied to many situations where transport takes place in a 2D layer surrounded by a 3D system of impurities. Charge hops within the 3D dopant system can give rise to the effective energy fluctuations on transport sites leading to the transport mechanism suggested in this report. Therefore we think that Eqs.(15),(16) might provide a theoretical explanation for recent experimental data that show in some cases a universal prefactor e^2/h in the exponential temperature dependence of the 2D hopping conductivity at low temperatures [12]. More study is needed, of course, to clarify this question.

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